

AMENDMENTS TO THE CLAIMS

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1. (Currently Amended) A high-frequency semiconductor device comprising:

a semiconductor substrate having a main surface;

a first wiring provided over said main surface of said semiconductor substrate;

and

a conductor layer continuously covering a periphery of said first wiring with a first insulator interposed therebetween in a section crossing a direction of extension of said first wiring, wherein said conductor layer always transmits a grounding potential.

2. (Original) The high-frequency semiconductor device according to claim 1, further comprising a second wiring provided over said main surface of said semiconductor substrate with an insulating film interposed therebetween,

said conductor layer continuously covering upper and side surfaces of said second wiring with a second insulator interposed therebetween in a section crossing a direction of extension of said second wiring and being connected to said semiconductor substrate.

3. (Original) The high-frequency semiconductor device according to claim 1, wherein an upper surface of said conductor layer is flat.

4. (Canceled)

5. (Original) The high-frequency semiconductor device according to claim 2, wherein said conductor layer continuously covers a periphery of said second wiring in

cooperation with said semiconductor substrate with said second insulator and said insulating film interposed therebetween in said section crossing said direction of extension of said second wiring.

6. (Original) The high-frequency semiconductor device according to claim 1, wherein said first wiring is electrically connected to said semiconductor substrate through a conductor plug filled in a through hole selectively formed in said conductor layer with a side insulating film interposed therebetween in a part taken in said direction of extension of said first wiring.

7. (Original) The high-frequency semiconductor device according to claim 2, wherein a portion of said second insulator which covers said upper and side surfaces of said second wiring and is provided in contact with said conductor layer is formed of the same material.

8. (Original) The high-frequency semiconductor device according to claim 1, wherein a portion of said first insulator which covers upper and side surfaces of said first wiring and is provided in contact with said conductor layer is formed of the same material.

Claims 9-16 (Withdrawn)